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(54) **Title**: METHOD FOR PRODUCING A STACK OF SEMI-CONDUCTOR THIN FILMS

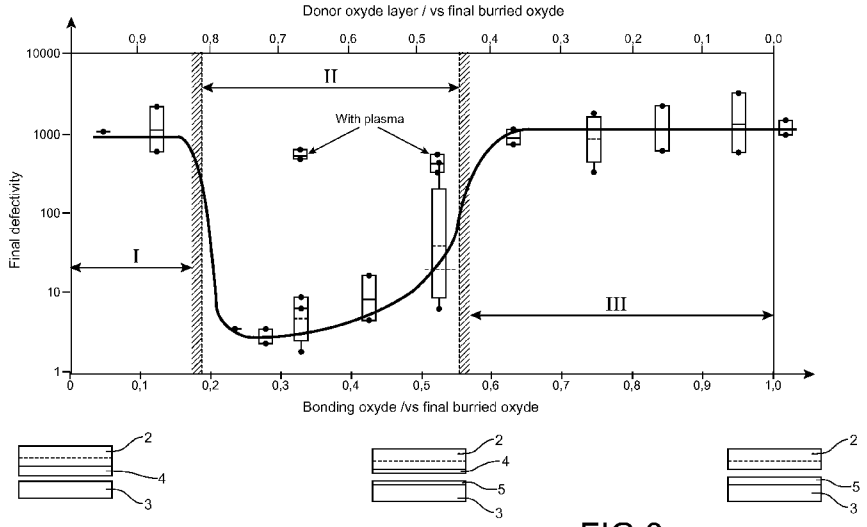


FIG.3

(57) **Abstract**: Method for producing stacked UTBOX-like semi-conductor structures, said method comprising: a) the formation of an electrical insulator layer on a donor substrate, b) the introduction of elements into the donor substrate through the insulator layer, c) the formation of an electrical insulator layer, on a second substrate known as final substrate, d) the bonding of the two substrates, the two insulator layers limiting the diffusion of water and forming an insulator layer buried between the two substrates, of thickness less than 50 nm, the donor oxide layer having, during the bonding, a thickness at least equal to that of the bonding oxide layer.

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